

Planetary Reactor® AIX G5+ for GaN on 200 mm Si

AIXTRON



Productivity and Performance

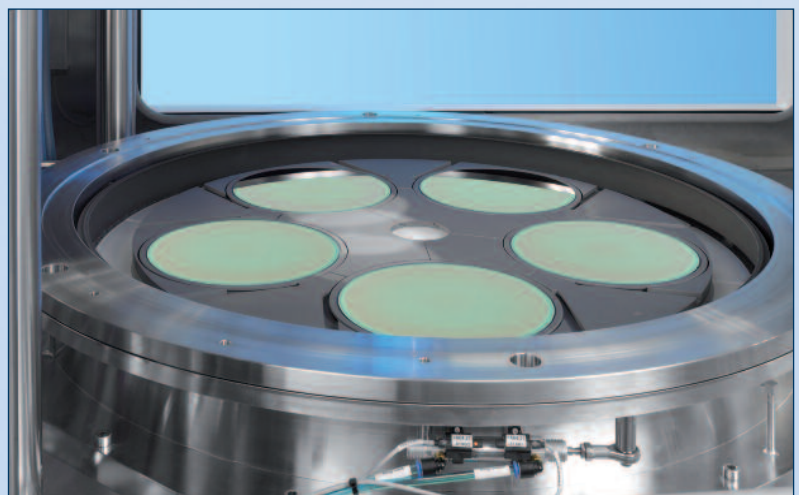


AIX G5+ System

Increase your productivity and performance.

Take advantage of G5+ for high-performance and low-cost GaN-on-Si devices:

- Dedicated technology package for GaN on 200 mm Si
- Compatible with the AIX G5 HT platform
- Enables Si-style mass manufacturing including chamber reset
- Planetary Reactor® Technology
 - Excellent and symmetric uniformities
 - Controlled bow behavior
 - Using standard Si substrates



AIX G5+ Reactor 5 x 200 mm

ALWAYS ONE STEP AHEAD

Planetary Reactor®

AIX G5+ for GaN on 200 mm Si

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AIX G5 Series GaN on Si characteristics

- Unique axis symmetric wafer performance like Si single wafer reactor
 - Wafer bow
 - Thickness, composition, concentration
 - Device yield
- Warm ceiling results in lowest heat flux through wafer
 - smallest wafer bow by vertical temperature gradient
 - Enabling standard Si wafer thickness
- In-situ temperature profile tweaking by individual GFR control
- Customized temperature optimization by recess shaping

